

IN THE SPECIFICATION

Delete the title and insert --Trenched Gate Non-Volatile Semiconductor Method With the Source/Drain Regions Spaced From the Trench by Sidewall Dopings--

Amend the specification by inserting immediately after the the section titled RELATED APPLICATIONS:

--This is a divisional of co-pending application Serial No. 09/052,057 filed on March 30, 1998, which is incorporated by reference herein in its entirety.--

Kindly amend:

Page 1, lines 9-10, delete "Ser. No. _____," and insert -- Ser. No. 09/052,051,--; and

Page 1, line 10, delete the first occurrence of " '[TITLE]' " and insert -- "A Trenched Gate Metal Oxide Semiconductor Device and Method"--;

Page 1, line 10, after the first occurrence of " '[TITLE]' " please insert --Ser. No. 09/052,058. "Trenched Gate Semiconductor Device and Method for Low Power Applications";--

Page 1, line 10, delete the second occurrence of "Ser. No. _____," and insert -- Ser. No. 09/052,062, --; and

Page 1, line 10, delete the second occurrence of " '[TITLE]' " and insert --"A Trenched Gate Non-Volatile Semiconductor Device and Method With Corner Doping and Sidewall Doping"--.

IN THE CLAIMS:

Please cancel claims 1-15.